# **RF2047**

# **GENERAL PURPOSE AMPLIFIER**

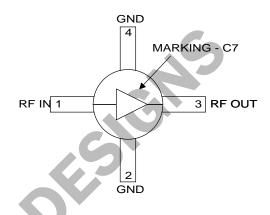
RoHS Compliant & Pb-Free Product Package Style: Micro-X Ceramic

### **Features**

- DC to 6000MHz Operation
- Internally matched Input and Output
- 16dB Small Signal Gain
- +26dBm Output IP3
- +12dBm Output Power
- Excellent Gain Flatness

# **Applications**

- Broadband, Low Noise Gain Blocks
- IF or RF Buffer Amplifiers
- Driver Stage for Power Amplifiers
- Final PA for Low Power Applications
- High Reliability Applications
- Broadband Test Equipment



Functional Block Diagram

# **Product Description**

The RF2047 is a general purpose, low cost RF amplifier IC. The device is manufactured on an advanced Gallium Arsenide Heterojunction Bipolar Transistor (HBT) process, and has been designed for use as an easily-cascadable  $50\Omega$  gain block. Applications include IF and RF amplification in wireless voice and data communication products operating in frequency bands up to  $6000\,\text{MHz}$ . The device is self-contained with  $50\Omega$  input and output impedances and requires only two external DC biasing elements to operate as specified. With a goal of enhanced reliability, the extremely small Micro-X ceramic package offers significantly lower thermal resistance than similar size plastic packages.

## **Ordering Information**

RF2047 General Purpose Amplifier
RF2047PCBA-41X Fully Assembled Evaluation Board

# **Optimum Technology Matching® Applied**

<b>▼</b> GaAs HBT	☐ SiGe BiCMOS	☐ GaAs pHEMT	☐ GaN HEMT
☐ GaAs MESFET	☐ Si BiCMOS	☐ Si CMOS	
☐ InGaP HBT	☐ SiGe HBT	☐ Si BJT	

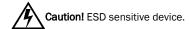
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# **RF2047**



# **Absolute Maximum Ratings**

Parameter	Rating	Unit
Input RF Power	+13	dBm
Operating Ambient Temperature	-40 to +85	°C
Storage Temperature	-60 to +150	°C



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RoHS status based on EUDirective 2002/95/EC (at time of this document revision).

Davamatar	Specification		Heit	Condition		
Parameter	Min.	Тур.	Max.	Unit	Condition	
Overall					T=25 °C, V <sub>D</sub> =3.6V, I <sub>CC</sub> =40 mA	
Frequency Range		DC to 6000		MHz		
3dB Bandwidth		>6		GHz		
Gain		16.0		dB 💧	Freq = 100 MHz	
		15.9		dB	Freq=1000MHz	
	14.0	15.8		dB	Freq=2000MHz	
		15.2		dB	Freq=3000MHz	
		14.5		dB	Freq=4000MHz	
		13.5		dB	Freq=6000MHz	
Gain Flatness		±0.1		dB	100MHz to 2000MHz	
Noise Figure		3.6		dB	Freq=2000MHz	
Input VSWR		<1.6:1	7		In a $50\Omega$ system, DC to $3000  \text{MHz}$	
		<1.2:1			In a $50\Omega$ system, $3000\text{MHz}$ to $6000\text{MHz}$	
Output VSWR		<1.5:1			In a $50\Omega$ system, DC to $3000  \text{MHz}$	
		<1.5:1			In a $50\Omega$ system, $3000\text{MHz}$ to $6000\text{MHz}$	
Output IP <sub>3</sub>		+26		dBm	Freq=2000MHz±50kHz, P <sub>TONE</sub> =-10dBm	
Output P <sub>1dB</sub>		+12.2		dBm	Freq=2000MHz	
Reverse Isolation	1	18.7		dB	Freq=2000MHz	
Thermal					I <sub>CC</sub> =40mA, P <sub>DISS</sub> =135mW (See Note 1.)	
Theta <sub>JC</sub>		332		°C/W	V <sub>PIN</sub> =3.37V	
Maximum Measured Junction Temperature at DC Bias Conditions		130		°C		
Mean Time To Failure		65,000		years	T <sub>AMB</sub> =+85 °C	
Power Supply					With 22Ω bias resistor, T=+25°C	
Device Operating Voltage	3.0	3.6	4.0	V	At pin 3 with I <sub>CC</sub> =40mA	
	3.9	4.5	4.9	V	At evaluation board connector, I <sub>CC</sub> =40 mA	
Operating Current			40	mA	See Note 2.	

## NOTES:

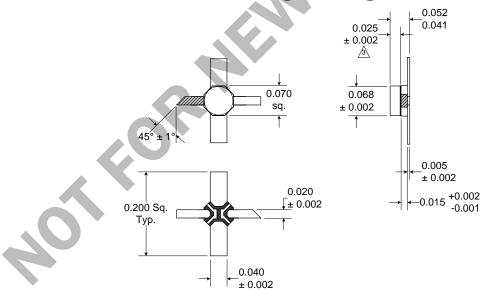
Note 1: The RF2047 must be operated at or below 40 mA in order to achieve the thermal performance stated above. Operating at 40 mA will ensure the best possible combination of reliability and electrical performance.

Note 2: Because of process variations from part to part, the current resulting from a fixed bias voltage will vary. As a result, caution should be used in designing fixed voltage bias circuits to ensure the worst case bias current does not exceed 40 mA over all intended operating conditions.



Pin	Function	Description	Interface Schematic
1	RF IN	RF input pin. This pin is NOT internally DC-blocked. A DC-blocking capacitor, suitable for the frequency of operation, should be used in most applications. DC-coupling of the input is not allowed, because this will override the internal feedback loop and cause temperature instability.	
2	GND	Ground connection. For best performance, keep traces physically short and connect immediately to ground plane.	
3	RF OUT	RF output and bias pin. Biasing is accomplished with an external series resistor and choke inductor to $V_{CC}$ . The resistor is selected to set the DC current into this pin to a desired level. The resistor value is determined by the following equation: $R = \frac{(V_{SUPPLY} - V_{DEVICE})}{I_{CC}}$ Care should also be taken in the resistor selection to <b>ensure that the current into the part never exceeds 40 mA over the planned operating temperature.</b> This means that a resistor between the supply and this pin is always required, even if a supply near 3.6V is available, to provide DC feedback to prevent thermal runaway. Because DC is present on this pin, a DC-blocking capacitor, suitable for the frequency of operation, should be used in most applications. The supply side of the bias network should also be well bypassed.	RF INO
4	GND	Same as pin 2.	

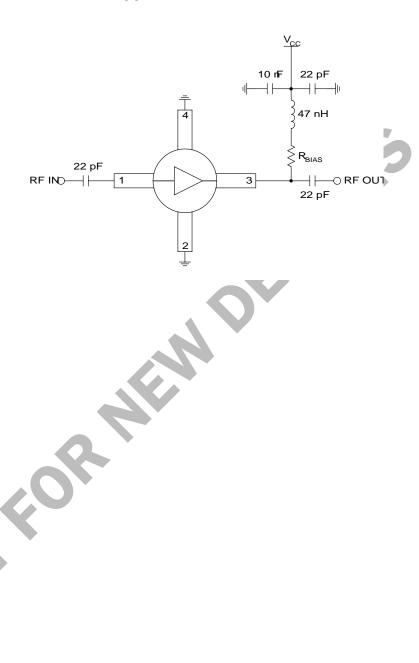
# Package Drawing



- NOTES:
  1. Shaded lead is pin 1.
  2. Darkened areas are metallization.
- Dimension applies to ceramic lid minus epoxy coating.



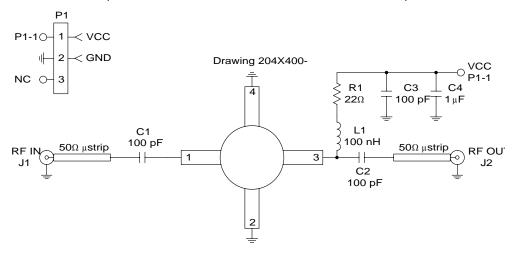
# **Application Schematic**



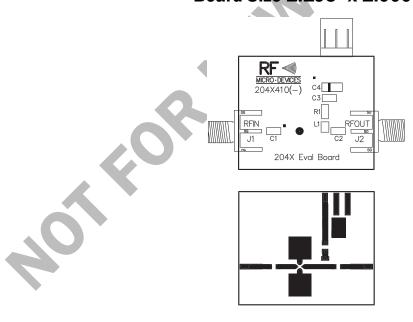


# **Evaluation Board Schematic**

(Download Bill of Materials from www.rfmd.com.)

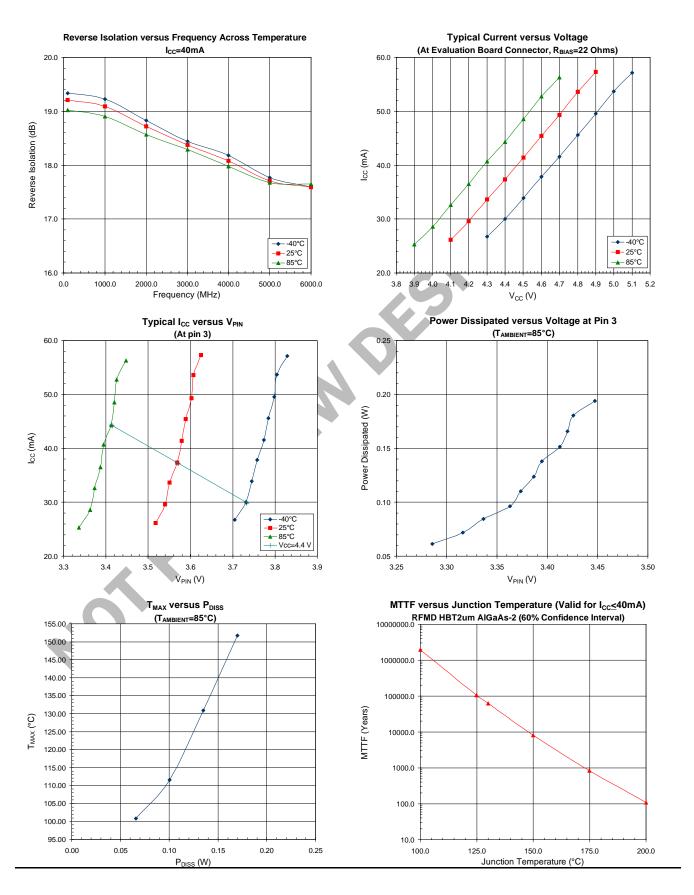


# Evaluation Board Layout Board Size 1.195" x 1.000"

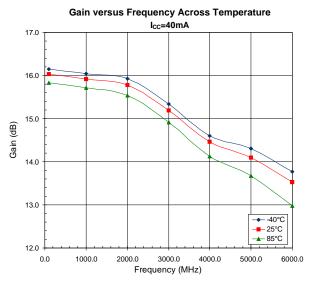


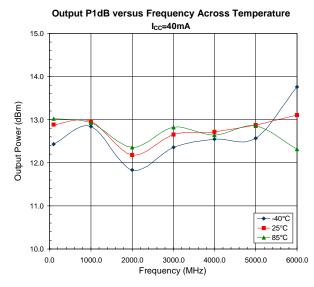
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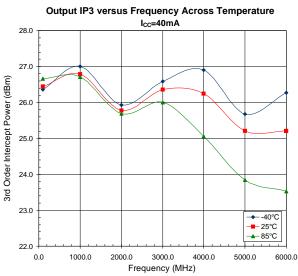


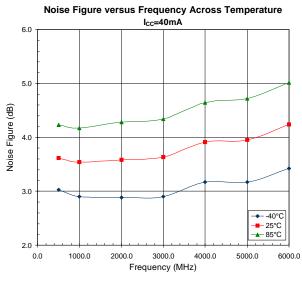


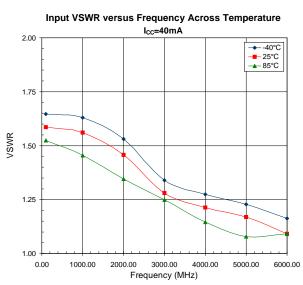


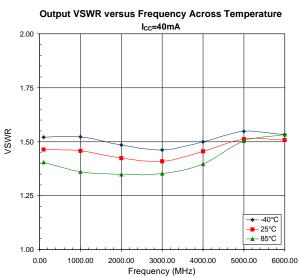














# **PCB Design Requirements**

### **PCB Surface Finish**

The PCB surface finish used for RFMD's qualification process is Electroless Nickel, immersion Gold. Typical thickness is  $3\mu$ inch to  $8\mu$ inch Gold over  $180\mu$ inch Nickel.

### **PCB Land Pattern Recommendation**

PCB land patterns are based on IPC-SM-782 standards when possible. The pad pattern shown has been developed and tested for optimized assembly at RFMD; however, it may require some modifications to address company specific assembly processes. The PCB land pattern has been developed to accommodate lead and package tolerances.

### **PCB Metal Land Mask Pattern**

 $A = 1.90 \times 1.14 \text{ Typ.}$  $B = 0.63 \times 1.90 \text{ Typ.}$ 

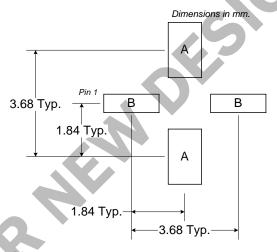


Figure 1. PCB Metal Land Pattern - RF204X (Top View)



### **PCB Solder Mask Pattern**

Liquid Photo-Imageable (LPI) solder mask is recommended. The solder mask footprint will match what is shown for the PCB metal land pattern with a 2mil to 3mil expansion to accommodate solder mask registration clearance around all pads. The center-grounding pad shall also have a solder mask clearance. Expansion of the pads to create solder mask clearance can be provided in the master data or requested from the PCB fabrication supplier.

A = 2.06 x 1.30 Typ.
B = 0.79 x 2.06 Typ.

Dimensions in mm.

A

3.68 Typ.

B

1.84 Typ.

A

B

A

3.68 Typ.

1.84 Typ.

Figure 2. PCB Solder Mask - RF204X (Top View)



